

DATA SHEET

PEMD13; PUMD13

**NPN/PNP resistor-equipped
transistors; R1 = 4.7 k Ω , R2 = 47 k Ω**

Product specification
Supersedes data of 2001 Feb 27

2003 Oct 08

NPN/PNP resistor-equipped transistors;
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FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- Control of IC inputs.

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | TYP. | MAX. | UNIT |
|------------------|---------------------------|------|------|------|
| V _{CEO} | collector-emitter voltage | – | 50 | V |
| I _O | output current (DC) | – | 100 | mA |
| TR1 | NPN | – | – | – |
| TR2 | PNP | – | – | – |
| R1 | bias resistor | 4.7 | – | kΩ |
| R2 | bias resistor | 47 | – | kΩ |

DESCRIPTION

NPN/PNP resistor-equipped transistors (see “Simplified outline, symbol and pinning” for package details).

PRODUCT OVERVIEW

| TYPE NUMBER | PACKAGE | | MARKING CODE | PNP/PNP COMPLEMENT | NPN/PNP COMPLEMENT |
|-------------|---------|-------|--------------------|--------------------|--------------------|
| | PHILIPS | EIAJ | | | |
| PEMD13 | SOT666 | | Z1 | PEMB13 | PEMH13 |
| PUMD13 | SOT363 | SC-88 | 3*1 ⁽¹⁾ | PUMB13 | PUMH13 |

Note

- * = p: Made in Hong Kong.
 * = t: Made in Malaysia.
 * = W: Made in China.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

| TYPE NUMBER | SIMPLIFIED OUTLINE AND SYMBOL | PINNING | |
|------------------|-------------------------------|---------|---------------|
| | | PIN | DESCRIPTION |
| PEMD13 PUMD13 | <p>Top view</p> <p>MAM468</p> | 1 | emitter TR1 |
| | | 2 | base TR1 |
| | | 3 | collector TR2 |
| | | 4 | emitter TR2 |
| | | 5 | base TR2 |
| | | 6 | collector TR1 |

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ORDERING INFORMATION

| TYPE NUMBER | PACKAGE | | |
|-------------|---------|--|---------|
| | NAME | DESCRIPTION | VERSION |
| PEMD13 | – | plastic surface mounted package; 6 leads | SOT666 |
| PUMD13 | – | plastic surface mounted package; 6 leads | SOT363 |

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--|---|--|------|------|------------------|
| Per transistor; for the PNP transistor with negative polarity | | | | | |
| V_{CBO} | collector-base voltage | open emitter | – | 50 | V |
| V_{CEO} | collector-emitter voltage | open base | – | 50 | V |
| V_{EBO} | emitter-base voltage | open collector | – | 10 | V |
| V_I | input voltage TR1 positive negative | | – | +30 | V |
| | | | – | –5 | V |
| V_I | input voltage TR2 positive negative | | – | +5 | V |
| | | | – | –30 | V |
| I_O | output current (DC) | | – | 100 | mA |
| I_{CM} | peak collector current | | – | 100 | mA |
| P_{tot} | total power dissipation | $T_{amb} \leq 25 \text{ }^\circ\text{C}$ | | | |
| | SOT363 | note 1 | – | 200 | mW |
| | SOT666 | notes 1 and 2 | – | 200 | mW |
| T_{stg} | storage temperature | | –65 | +150 | $^\circ\text{C}$ |
| T_j | junction temperature | | – | 150 | $^\circ\text{C}$ |
| T_{amb} | operating ambient temperature | | –65 | +150 | $^\circ\text{C}$ |
| Per device | | | | | |
| P_{tot} | total power dissipation | $T_{amb} \leq 25 \text{ }^\circ\text{C}$ | | | |
| | SOT363 | note 1 | – | 300 | mW |
| | SOT666 | notes 1 and 2 | – | 300 | mW |

Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
2. Reflow soldering is the only recommended soldering method.

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THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------------------|---|--|-------|------|
| Per transistor | | | | |
| $R_{th\ j-a}$ | thermal resistance from junction to ambient | $T_{amb} \leq 25 \text{ }^\circ\text{C}$ | | |
| | SOT363 | note 1 | 625 | K/W |
| | SOT666 | notes 1 and 2 | 625 | K/W |
| Per device | | | | |
| $R_{th\ j-a}$ | thermal resistance from junction to ambient | $T_{amb} \leq 25 \text{ }^\circ\text{C}$ | | |
| | SOT363 | note 1 | 416 | K/W |
| | SOT666 | notes 1 and 2 | 416 | K/W |

Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--|--------------------------------------|--|------|------|------|------------------|
| Per transistor; for the PNP transistor with negative polarity | | | | | | |
| I_{CBO} | collector-base cut-off current | $V_{CB} = 50 \text{ V}$; $I_E = 0$ | – | – | 100 | nA |
| I_{CEO} | collector-emitter cut-off current | $V_{CE} = 30 \text{ V}$; $I_B = 0$ | – | – | 1 | μA |
| | | $V_{CE} = 30 \text{ V}$; $I_B = 0$; $T_j = 150 \text{ }^\circ\text{C}$ | – | – | 50 | μA |
| I_{EBO} | emitter-base cut-off current | $V_{EB} = 5 \text{ V}$; $I_C = 0$ | – | – | 170 | μA |
| h_{FE} | DC current gain | $V_{CE} = 5 \text{ V}$; $I_C = 10 \text{ mA}$ | 100 | – | – | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = 5 \text{ mA}$; $I_B = 0.25 \text{ mA}$ | – | – | 100 | mV |
| $V_{i(off)}$ | input-off voltage | $I_C = 100 \text{ } \mu\text{A}$; $V_{CE} = 5 \text{ V}$ | – | 0.6 | 0.5 | V |
| $V_{i(on)}$ | input-on voltage | $I_C = 5 \text{ mA}$; $V_{CE} = 0.3 \text{ V}$ | 1.3 | 0.9 | – | V |
| R1 | input resistor | | 3.3 | 4.7 | 6.1 | $\text{k}\Omega$ |
| $\frac{R2}{R1}$ | resistor ratio | | 8 | 10 | 12 | |
| C_c | collector capacitance | $I_E = i_e = 0$; $V_{CB} = 10 \text{ V}$; $f = 1 \text{ MHz}$ | | | | |
| | TR1 (NPN) | | – | – | 2.5 | pF |
| | TR2 (PNP) | | – | – | 3 | pF |

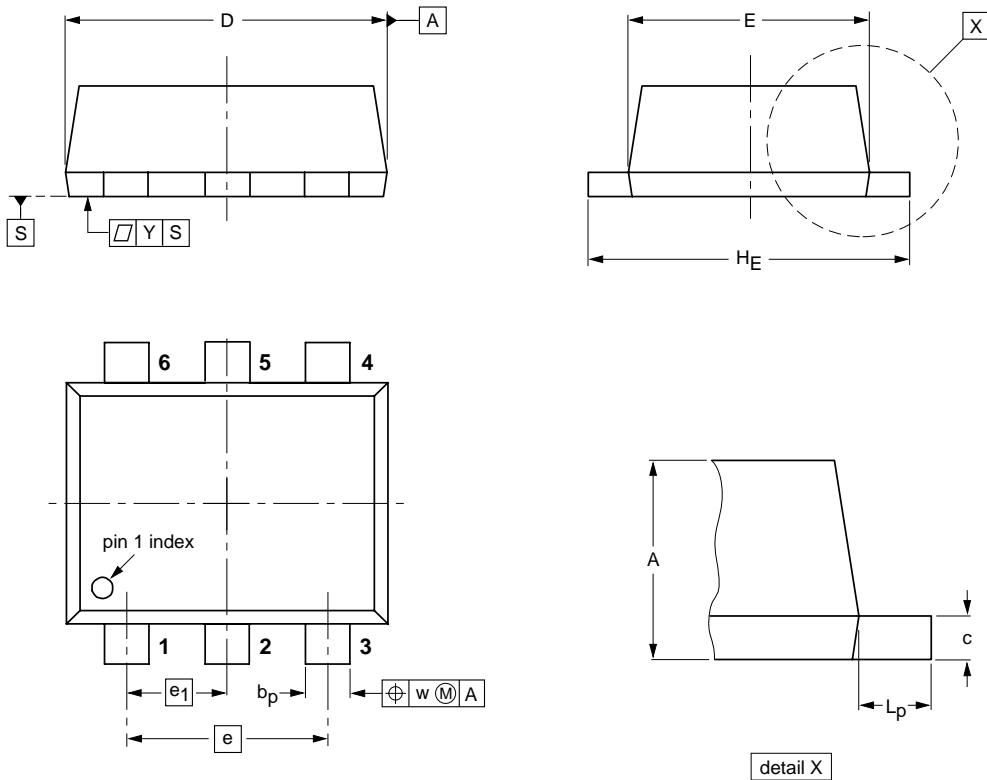
NPN/PNP resistor-equipped transistors;
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PACKAGE OUTLINES

Plastic surface mounted package; 6 leads

SOT666



DIMENSIONS (mm are the original dimensions)

| UNIT | A | b_p | c | D | E | e | e_1 | H_E | L_p | w | y |
|------|------------|--------------|--------------|------------|------------|-----|-------|------------|------------|-----|-----|
| mm | 0.6 0.5 | 0.27 0.17 | 0.18 0.08 | 1.7 1.5 | 1.3 1.1 | 1.0 | 0.5 | 1.7 1.5 | 0.3 0.1 | 0.1 | 0.1 |

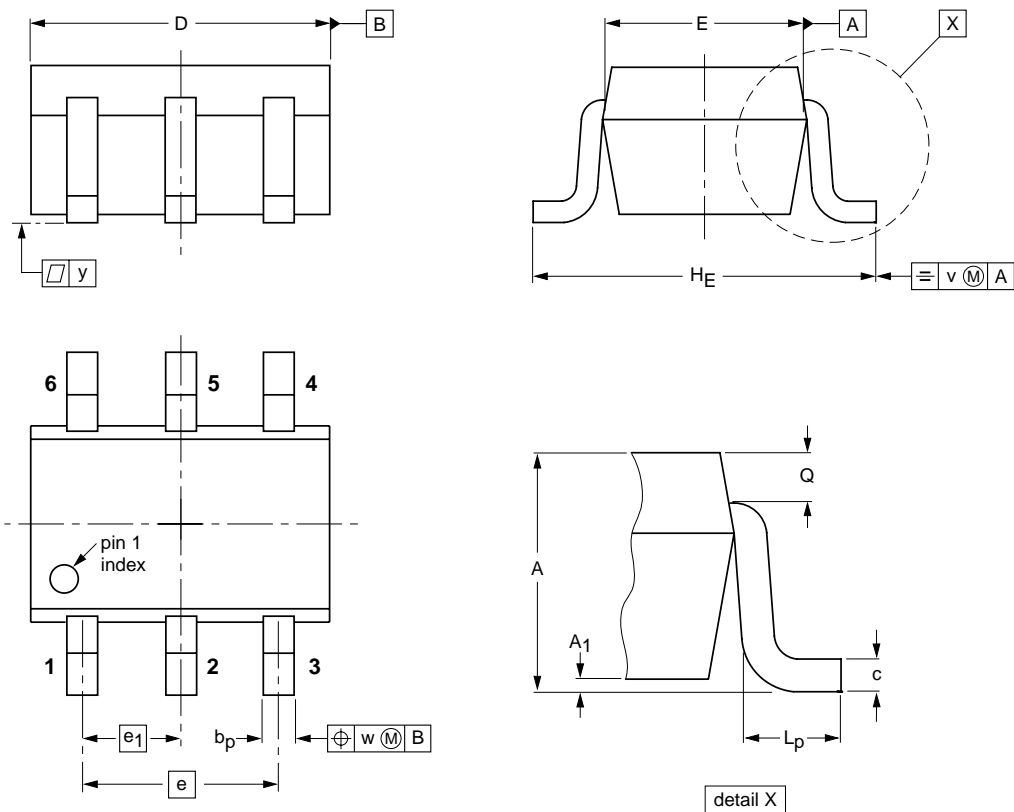
| OUTLINE VERSION | REFERENCES | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|------|---------------------|----------------------|
| | IEC | JEDEC | EIAJ | | |
| SOT666 | | | | | 01-01-04 01-08-27 |

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DIMENSIONS (mm are the original dimensions)

| UNIT | A | A1 max | bp | c | D | E | e | e1 | HE | Lp | Q | v | w | y |
|------|------------|-----------|--------------|--------------|------------|--------------|-----|------|------------|--------------|--------------|-----|-----|-----|
| mm | 1.1 0.8 | 0.1 | 0.30 0.20 | 0.25 0.10 | 2.2 1.8 | 1.35 1.15 | 1.3 | 0.65 | 2.2 2.0 | 0.45 0.15 | 0.25 0.15 | 0.2 | 0.2 | 0.1 |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|--------------------|------------|-------|-------|--|------------------------|------------|
| | IEC | JEDEC | EIAJ | | | |
| SOT363 | | | SC-88 | | | 97-02-28 |

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DATA SHEET STATUS

| LEVEL | DATA SHEET STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾⁽³⁾ | DEFINITION |
|-------|----------------------------------|----------------------------------|--|
| I | Objective data | Development | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice. |
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